What is claimed is:

1	1. A system comprising:		
2	a high-density non-volatile fast memory; and		
3	an ultraviolet (UV) light window adapted to expose the high-density non-volatile		
4	fast memory to UV light.		
1	2. The system of claim 1, wherein the high-density non-volatile fast memory		
2	comprises a modified flash memory having no erasing circuitry.		
1	3. The system of claim 1, wherein the high-density non-volatile fast memory		
2	comprises a two-terminal drain-gate-connected modified flash cell having no erasing		
3	circuitry.		
1	4. The system of claim 3, wherein the two-terminal drain-gate-connected		
2	modified flash cell is a diode-connected nitrided read-only memory (NROM) cell.		
1	5. A device comprising:		
2	two-terminal drain-gate-connected modified flash cells having no erasing		
3	circuitry; and		
4	an ultraviolet (UV) light window adapted to expose the two-terminal drain-gate-		
5	connected modified flash cells to UV light.		
1	6. The device of claim 5, wherein the two-terminal drain-gate-connected		
2	modified flash cells are configured as a two-dimensional planar matrix of cells.		

1	7. The device of claim 6, wherein the two-dimensional planar matrix of cell				
2	is a NAND configuration.				
1	8. The device of claim 6, wherein the two-dimensional planar matrix of cell				
2	is a NOR configuration.				
1	9. The device of claim 5, wherein the two-terminal drain-gate-connected				
2	gate-connected				
۷	modified flash cells are configured as three-dimensional layers.				
1	10. A system comprising:				
2	modified flash cells having no erasing circuitry; and				
3	an ultraviolet (UV) light window adapted to expose the modified flash cells to UV				
4	light.				
1	11. The system of claim 10, wherein the UV light window is located above a				
2	control gate of the modified flash cells.				
1	12. The system of claim 10, wherein the UV light window is located below a				
2	substrate of the modified flash cells.				
1	13. The system of claim 10, wherein the UV light window is interposed				
2	between control gates of the modified flash cells.				
1	14. The system of claim 10, wherein the UV light window is offset from				
2	control gates of the modified flash cells.				

1	15.	The system of claim 10, wherein the UV light window is adapted to		
2	diffuse UV lig	ght entering the UV light window.		
1	16.	The system of claim 10, wherein the modified flash cells are arranged in a		
2	NAND config	guration.		
1	17.	The system of claim 10, wherein the modified flash cells are arranged in a		
2	NOR configuration.			
1	18.	The system of claim 10, wherein the modified flash cells are configured as		
2	a two-dimensi	ional planar matrix of cells.		
1	19.	The system of claim 18, wherein the two-dimensional planar matrix of		
2	cells is a NAN	ND configuration.		
1	20.	The system of claim 18, wherein the two-dimensional planar matrix of		
2	cells is a NOR	Configuration.		
1	21.	The system of claim 10, wherein the modified flash cells are configured as		
2	three-dimension	onal layers.		
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1	22.	The system of claim 21, wherein the three-dimensional layers comprise		
2	modified flash	cells arranged in a NAND configuration.		

I	23.	The system of claim 21, wherein the three-dimensional layers comprise
2	modified flash	cells arranged in a NOR configuration.
1	24.	The system of claim 10, further comprising an electronic device adapted to
2	house the mod	ified flash cells, the electronic device having an opening to receive the UV
3	light window.	
1	25.	The system of claim 24, wherein the electronic device is a portable
2	electronic devi	ce.
1	26.	The system of claim 25, wherein the portable electronic device is a cellular
2	telephone.	
1	27.	The system of claim 25, wherein the portable electronic device is a
2	personal digital	assistant (PDA).
1	28.	The system of claim 25, wherein the portable electronic device is an MP3
2	player.	
1		The system of claim 25, wherein the portable electronic device is a lap-top
2	computer.	
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1		A method comprising:
2		g a high-density non-volatile fast memory to ultraviolet (UV) light; and
3	erasing t	he high-density non-volatile fast memory using the UV light.

1	31. The method of claim 30 further comprising:				
2	passing light through a UV light window.				
1	32. A method comprising:				
2	exposing a modified flash cell to ultraviolet (UV) light; and				
3	erasing the modified flash cell using the UV light.				
1	33. A method comprising:				
2	installing ultraviolet (UV) windows onto portable electronic devices having non-				
3	volatile memory;				
4	passing UV light through the UV windows; and				
5	erasing the non-volatile memory by exposing the non-volatile memory to the UV				
6	light through the UV light windows.				
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1	34. A system comprising:				
2	means for exposing a modified flash cell to ultraviolet (UV) light; and				
3	means for erasing the modified flash cell using the UV light.				
1	35. A system comprising:				
2	means for installing ultraviolet (UV) windows onto portable electronic devices				
3	having non-volatile memory; and				
4	means for erasing the non-volatile memory by exposing the non-volatile memory				
5	to UV light through the UV light windows.				